LISTING OF CLAIMS
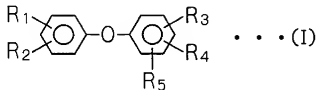
1.　　**(Currently amended)**　A developer composition for <u>positive</u> resists, comprising ~~an organic quaternary ammonium base as a main component~~ <u>a novolak resin and a naphthoquinone diazide compound, 2 to 5% by mass of tetramethylammonium hydroxide</u> and a surfactant <u>in an aqueous solution,</u>

said surfactant containing an anionic surfactant represented by the following general formula (I):

$$R_1 \diagdown \!\!\!\!\!\!\!\!\bigcirc\!\!\!\!\!\!\!\!\diagup O \diagdown \!\!\!\!\!\!\!\!\bigcirc \diagup R_3 \quad \cdot \cdot \cdot (I)$$
$$R_2 \diagup \qquad \qquad \diagdown R_4$$
$$\underset{R_5}{|}$$

wherein at least one member of R_1 and R_2 represents an alkyl or alkoxy group having 5 to 18 carbon atoms and any remaining member represents a hydrogen atom, or an alkyl or alkoxy group having 5 to 18 carbon atoms, and at least one member of R_3, R_4 and R_5 represents a group represented by the following general formula (II):

$$-SO_3M \quad \cdot \cdot \cdot \quad (II)$$

wherein M represents a metal atom <u>selected from the group consisting of sodium, potassium, and calcium</u>, and any remaining member represent a hydrogen atom or a group represented by the above general formula (II)<u>, provided that, in the general formula (I), when two or more groups represented by the general formula (II) are present, M may be the same or different, and wherein</u>

<u>the amount of said anionic surfactant is in the range of 1,000 to 50,000 ppm based on said developer composition</u>.

2.　　**(Canceled)**

3.　　**(Previously presented)**　A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer, selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 1 to form a resist pattern.

4.　　**(Previously presented)**　A method for formation of a resist pattern, comprising applying a resist composition on a substrate to form a resist layer, prebaking the resist layer,

selectively exposing the prebaked resist layer to light, and alkali-developing the exposed resist layer with the developer composition for resists according to claim 2 to form a resist pattern.